

**AMENDMENTS TO THE CLAIMS:**

*This listing of claims will replace all prior versions, and listings, of claims in the application:*

1. (Currently amended) A plasma process apparatus for performing a plasma process on a target substrate, the apparatus comprising:

a process chamber in which the target substrate is installed;

a gas inlet for introducing a gas into the process chamber; and

a plasma discharge production section for producing a plasma discharge provided in the process chamber,

wherein the plasma discharge production section includes a first electrode and a second electrode that is closer to the target substrate than the first electrode is,

wherein the first and second electrodes are on the same side of the target substrate; and

only surfaces of the first and second electrodes which can be seen in the normal line direction of the target substrate function as a plasma discharge surface.

2. (Currently amended) A plasma process apparatus for performing a plasma process on a target substrate, the apparatus comprising:

a process chamber in which the target substrate is installed;

a gas inlet for introducing a gas into the process chamber; and

a plasma discharge production section for producing a plasma discharge provided in the process chamber,

wherein the plasma discharge production section includes a first electrode, an insulating layer formed on a portion of an electrode surface of the first electrode, and a second electrode formed on the insulating layer.

3. (Previously presented) The plasma process apparatus according to claim 1, wherein the gas inlet is provided at the first electrode.

4. (Previously presented) The plasma process apparatus according to claim 1, wherein the first electrode has a concaved plasma discharge surface.

5. (Previously presented) The plasma process apparatus according to claim 1, wherein the area of a plasma discharge surface of the first electrode is larger than that of the second electrode.

6. (Currently amended) A plasma process apparatus for performing a plasma process on a target substrate, the apparatus comprising:

a process chamber in which the target substrate is installed;

a gas inlet for introducing a gas into the process chamber; and

a plasma discharge production section for producing a plasma discharge in the process chamber,

wherein the plasma discharge production section includes a first electrode and a second electrode that is closer to the target substrate than the first electrode is;

only surfaces of the first and second electrodes which can be seen in the normal line direction of the target substrate function as a plasma discharge surface; and

~~The plasma process apparatus according to claim 1, wherein the plasma discharge production section includes a plurality of plasma discharge surface regions of the first electrode and a plurality of plasma discharge surface regions of the second electrode.~~

7. (Currently amended) A plasma process apparatus for performing a plasma process on a target substrate, the apparatus comprising:

a process chamber in which the target substrate is installed;

a gas inlet for introducing a gas into the process chamber; and

a plasma discharge production section for producing a plasma discharge in the process chamber,

wherein the plasma discharge production section includes a first electrode and a second electrode that is closer to the target substrate than the first electrode is;

only surfaces of the first and second electrodes which can be seen in the normal line

direction of the target substrate function as a plasma discharge surface; and

~~The plasma process apparatus according to claim 1, wherein: wherein plasma discharge surface regions of the first electrode and plasma discharge surface regions of the second electrode are alternately provided along one planar direction of the target substrate; and the distance between the second electrode and the target substrate is greater than the distance between the adjacent second electrodes.~~

8. (Previously presented) The plasma process apparatus according to claim 1, further comprising a power source for applying electric energy to the first and second electrodes, wherein the frequency of the power source is equal to or higher than 100 kHz and equal to or lower than 300 MHz.

9-15. (Canceled)

16. (Currently amended) A plasma process apparatus for performing a plasma process on a target substrate, the apparatus comprising:  
a process chamber in which the target substrate is installed;  
a gas inlet for introducing a gas into the process chamber; and  
a plasma discharge production section for producing a plasma discharge in the process chamber,

wherein the plasma discharge production section includes a first electrode and a second electrode that is closer to the target substrate than the first electrode is;  
only surfaces of the first and second electrodes which can be seen in the normal line direction of the target substrate function as a plasma discharge surface; and  
~~The plasma process apparatus according to claim 1, wherein a plasma discharge surface of the first electrode has a concavely curved surface.~~

17. (Original) The plasma process apparatus according to claim 16, wherein a plasma discharge surface of the first electrode and a plasma discharge surface of the second electrode constitute portions of a continuously curved surface.

18. (Previously presented) The plasma process apparatus according to claim 1, wherein a plasma discharge surface of the first electrode has a plurality of cavities.

19. (Original) The plasma process apparatus according to claim 18, wherein a gas inlet is formed in a bottom of at least one of the cavities.

20. (Canceled)

21. (Currently amended) A plasma process apparatus for performing a plasma process on a target substrate, the apparatus comprising:  
a process chamber in which the target substrate is installed;  
a gas inlet for introducing a gas into the process chamber; and  
a plasma discharge production section for producing a plasma discharge in the process chamber,

wherein the plasma discharge production section includes a first electrode and a second electrode that is closer to the target substrate than the first electrode is;  
only surfaces of the first and second electrodes which can be seen in the normal line  
direction of the target substrate function as a plasma discharge surface; and

~~The plasma process apparatus according to claim 1, wherein the first electrode is provided with a plurality of concavities opened onto the target substrate.~~

22. (Original) The plasma process apparatus according to claim 21, wherein the shape of the opening of each concavity is rectangular.

23. (Original) The plasma process apparatus according to claim 21, wherein the shape of the opening of each concavity is circular.

24. (Original) A plasma process apparatus, comprising:  
a process chamber in which a target substrate is installed;  
a gas inlet for introducing a gas into the process chamber; and  
a plasma discharge production section provided in the process chamber for performing a plasma process on the target substrate,  
wherein the plasma discharge production section includes a plurality of insulators arranged in a stripe pattern extending along a direction parallel to the target substrate, first electrodes provided in at least areas between the adjacent insulators, and second electrodes provided at ends of the insulators which are closer to the target substrate such that the second electrodes are separated from the first electrodes.

25. (Original) The plasma process apparatus according to claim 24, wherein the first electrodes provided between the adjacent insulators are separated from each other.

26. (Original) The plasma process apparatus according to claim 24, wherein:  
a plurality of gas inlets are formed in the first electrode; and

the plurality of gas inlets are arranged along a direction that is not parallel to the longitudinal direction of the striped insulators.

27. (Original) The plasma process apparatus according to claim 25, wherein the plurality of gas inlets are arranged along a direction perpendicular to the longitudinal direction of the striped insulators.

28. (Original) The plasma process apparatus according to claim 26, wherein the gas inlets are designed to release a gas in directions parallel to each other.

29. (Original) The plasma process apparatus according to claim 26, wherein each gas inlet is designed to release a gas in a direction perpendicular to the plasma discharge surface of the first electrode.

30. (Original) The plasma process apparatus according to claim 26, wherein each gas inlet is designed to release a gas in a direction oblique with respect to the normal line direction of the target substrate.

31. (New) A plasma process apparatus for performing a plasma process on a target substrate, the apparatus comprising:

a process chamber in which the target substrate is installed;  
a gas inlet for introducing a gas into the process chamber; and

a plasma discharge production section, for producing a plasma discharge in the process chamber,

wherein the plasma discharge production section includes a first electrode, an insulating layer formed on a portion of an electrode surface of the first electrode that is closer to the target substrate, and a second electrode formed on the insulating layer.